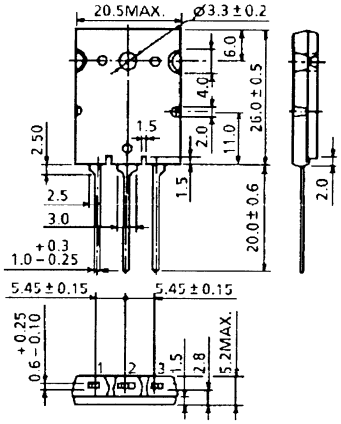
TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT40T302

Parallel Resonance Inverter Switching Applications

- FRD included between emitter and collector
- Enhancement mode
- High speed IGBT: t_f = 0.23 μs (typ.) (I_C = 40 A)
  FRD: t_{rr} = 0.7 μs (typ.) (di/dt = −20 A/μs)
- Low saturation voltage: $V_{CE\ (sat)}$ = 3.7 V (typ.) (I_C = 40 A)

Unit: mm



1. GATE
2. COLLECTOR (HEAT SINK)
3. EMITTER

JEDEC	—
JEITA	—
TOSHIBA	2-21F2C

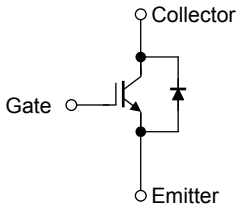
Weight: 9.75 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

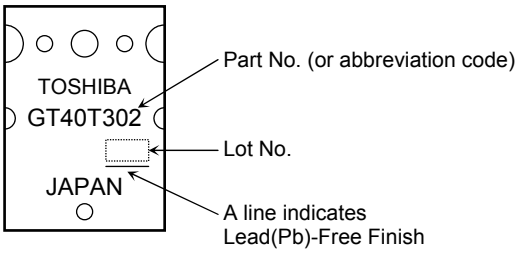
Characteristics		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	1500	V
Gate-emitter voltage		V_{GES}	±25	V
Collector current	DC	I_C	40	A
	1 ms	I_{CP}	80	
Diode forward current	DC	I_F	30	A
	1 ms	I_{FP}	80	
Collector power dissipation (Tc = 25°C)		P_C	200	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

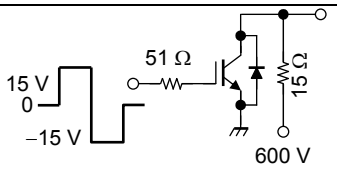
Equivalent Circuit



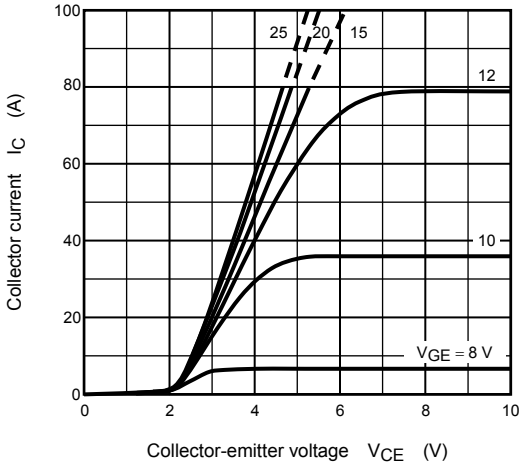
Marking



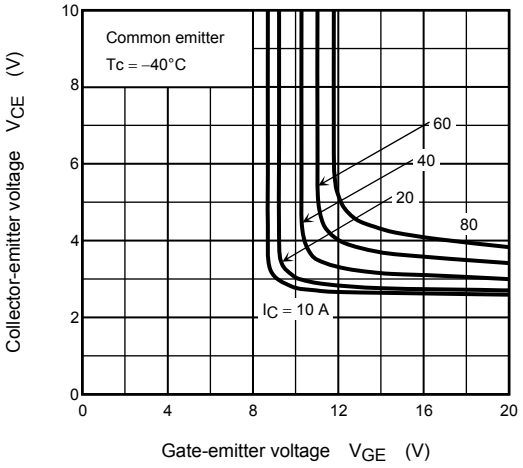
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	V_{GE} = ±25 V, V_{CE} = 0	—	—	±500	nA
Collector cut-off current		I_{CES}	V_{CE} = 1500 V, V_{GE} = 0	—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE\ (OFF)}$	I_C = 40 mA, V_{CE} = 5 V	4.0	—	7.0	V
Collector-emitter saturation voltage		$V_{CE\ (sat)}$	I_C = 40 A, V_{GE} = 15 V	—	3.7	5.0	V
Input capacitance		C_{ies}	V_{CE} = 10 V, V_{GE} = 0, f = 1 MHz	—	2900	—	pF
Switching time	Rise time	t_r		—	0.40	—	μs
	Turn-on time	t_{on}		—	0.45	—	
	Fall time	t_f		—	0.23	0.40	
	Turn-off time	t_{off}		—	0.6	—	
Diode forward voltage		V_F	I_F = 30 A, V_{GE} = 0	—	1.9	2.5	V
Reverse recovery time		t_{rr}	I_F = 30 A, V_{GE} = 0, di/dt = −20 A/μs	—	0.7	3.0	μs
Thermal resistance		$R_{th\ (j\text{-}c)}$	IGBT	—	—	0.625	°C/W
			Diode	—	—	1.25	

$I_C - V_{CE}$



$V_{CE} - V_{GE}$



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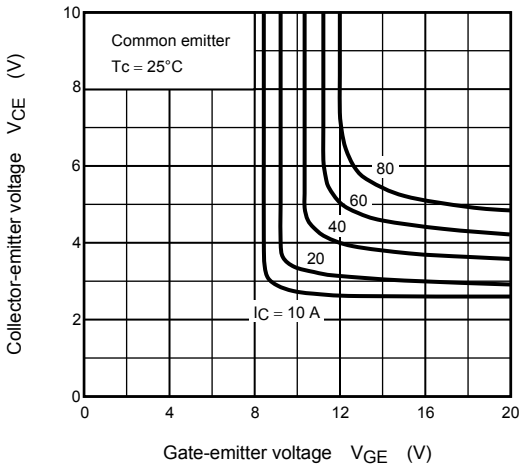
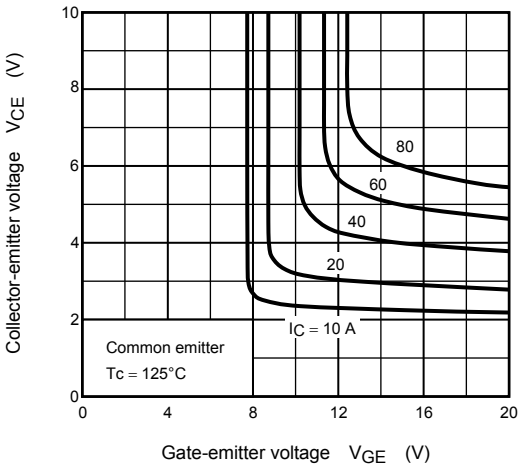
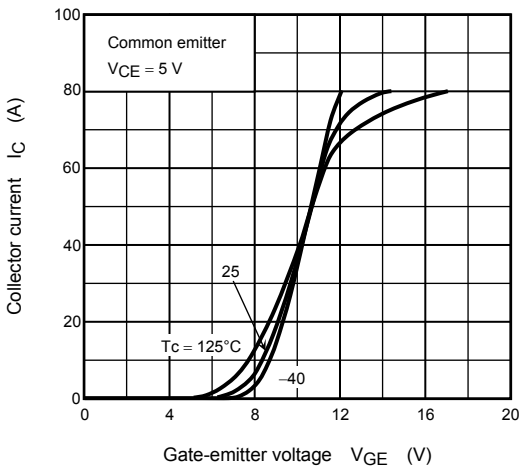


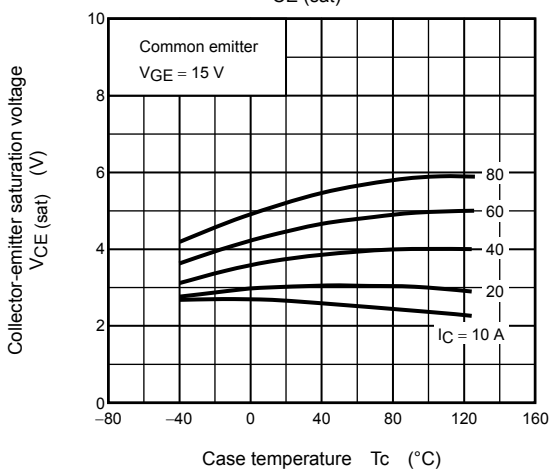
$V_{CE} - V_{GE}$



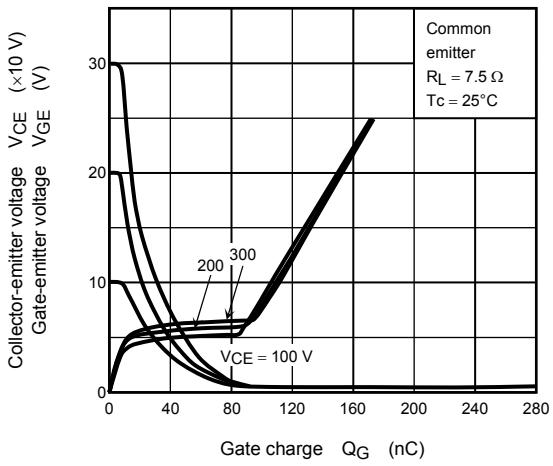
$I_C - V_{GE}$



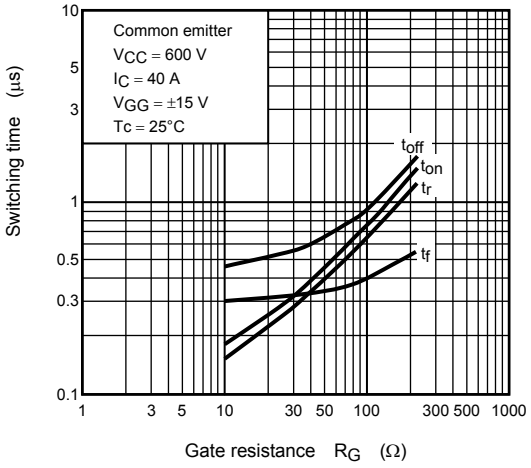
$V_{CE\ (sat)} - Tc$



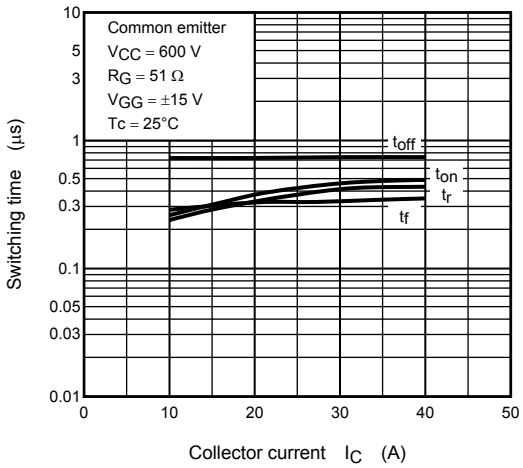
V_{CE}, V_{GE} – Q_G



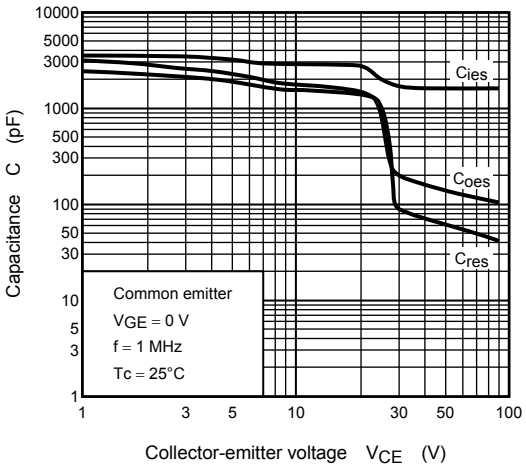
Switching time – R_G



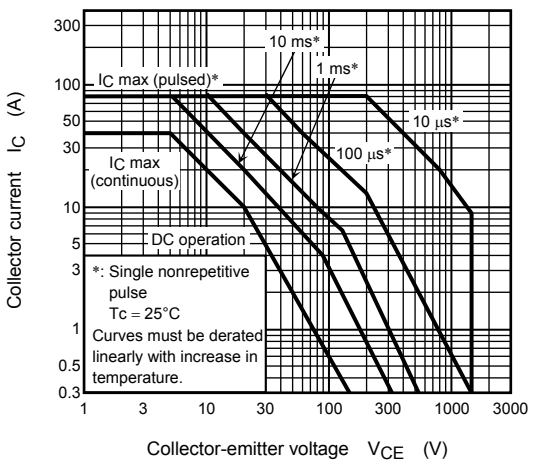
Switching time – I_C



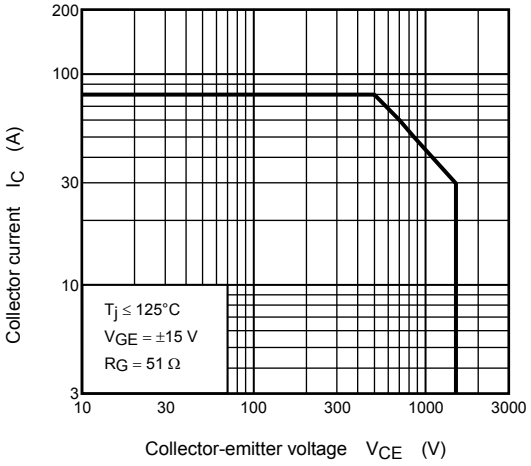
C – V_{CE}



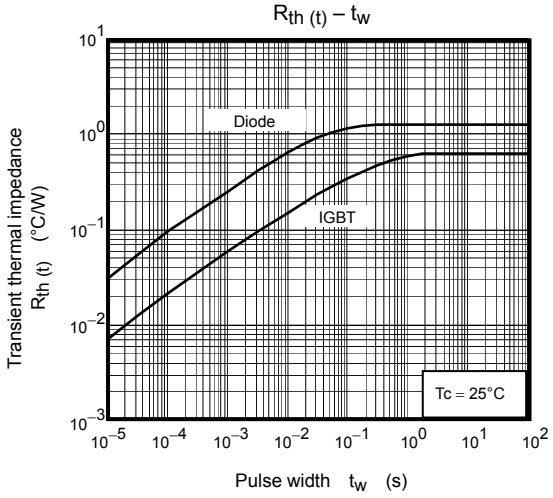
Safe operating area



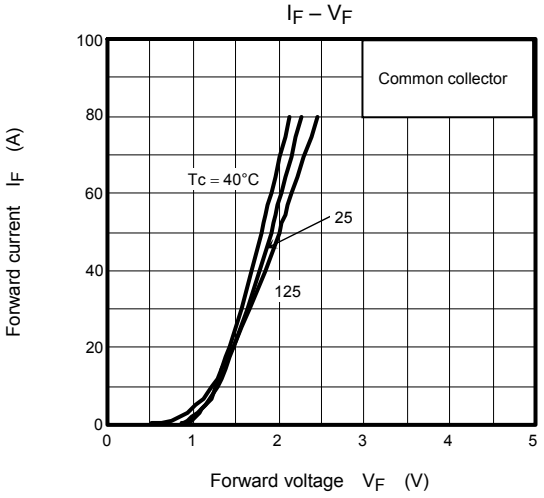
Reverse bias SOA



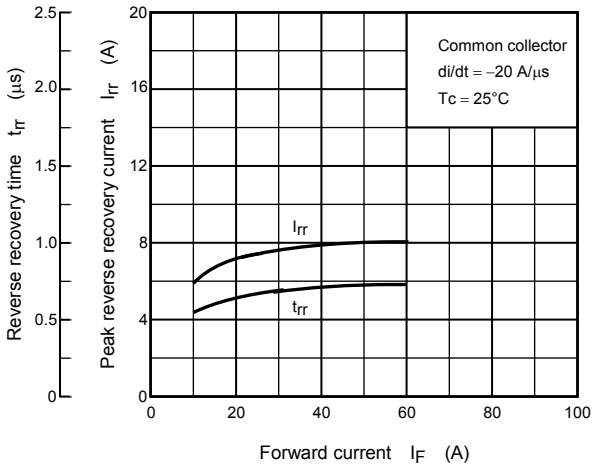
$R_{th\ (t)} - t_w$



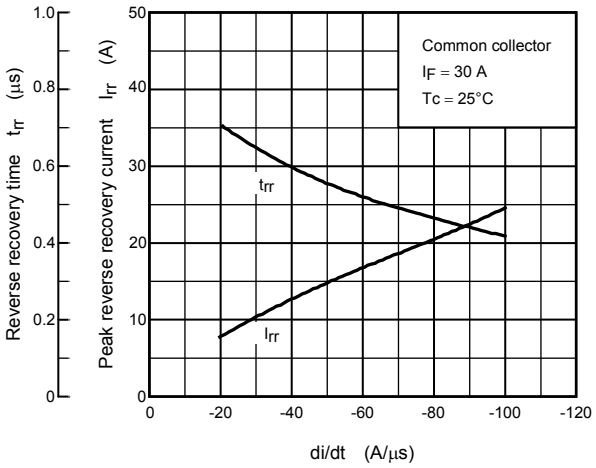
$I_F - V_F$



$I_{rr}, t_{rr} - I_F$



$I_{rr}, t_{rr} - di/dt$



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20070701-EN GENERAL

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